



#### P-CHANNEL ENHANCEMENT MODE MOSFET

# **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C
	$45m\Omega$ @ V <sub>GS</sub> = -4.5V	-4.3A
-20V	$58m\Omega$ @ VGS = -2.5V	-3.8A
	90mΩ @ V <sub>GS</sub> = -1.8V	-3.1A

# **Description**

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- DC-DC Converters
- Power Management Functions

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMP2045UQ)

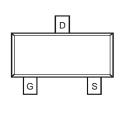
## **Mechanical Data**

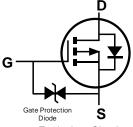
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 63
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)





SOT23 (Standard)





Top View

Top View

Equivalent Circuit

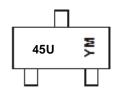
# **Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
DMP2045U-7	Standard	SOT23 (Standard)	3,000/Tape & Reel
DMP2045U-13	Standard	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

# **Marking Information**



 $45U = Product Type Marking Code YM or <math>\overline{Y}M = Date Code Marking Y or <math>\overline{Y} = Year (ex: I = 2021)$  M = Month (ex: 9 = September)

Date Code Key

Date Code Key												
Year	2017		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	E		I	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	-20	V	
Gate-Source Voltage		Vgss	±8	V
Continuous Drain Current (Note 6) Vgs = -4.5V	ID	-4.3 -3.5	А	
Maximum Continuous Body Diode Forward Current (	Is	-1.2	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	-25	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

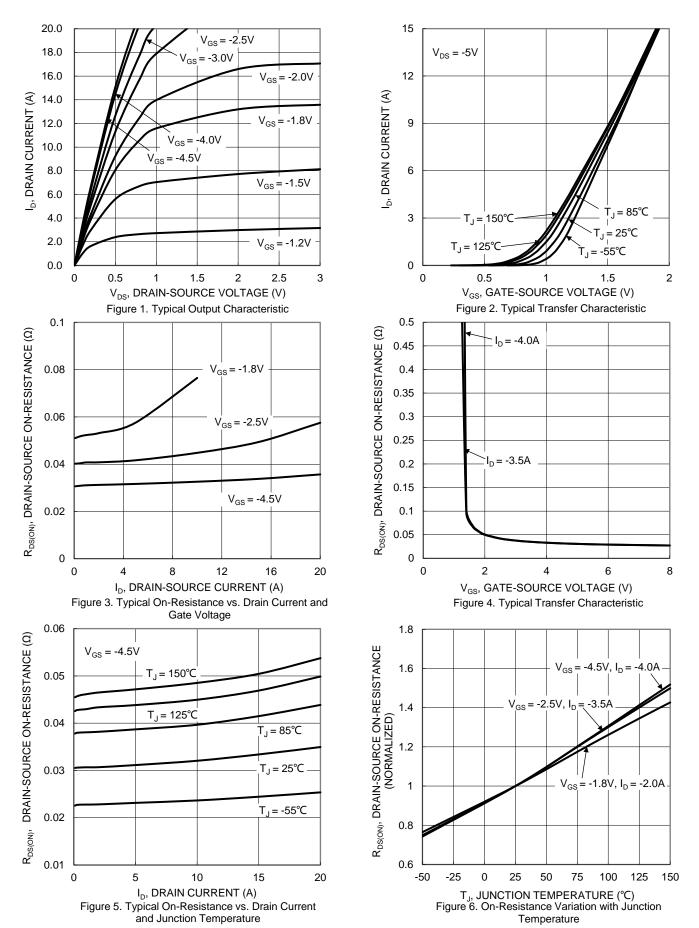
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	154	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	98	°C/W
Operating and Storage Temperature Range	·	TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	V <sub>G</sub> S = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	-1	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±10	μA	$V_{GS} = \pm 8.0 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
		_	32	45		V <sub>G</sub> S = -4.5V, I <sub>D</sub> = -4.0A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	42	58	mΩ	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3.5A
		_	54	90		VGS = -1.8V, ID = -1.0A
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		634	_	pF	
Output Capacitance	Coss		81	_	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	66	_	pF	1 - 1.000112
Gate Resistance	$R_g$	_	20	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge	$Q_g$	_	6.8	_	nC	
Gate-Source Charge	Qgs	_	0.7	_	nC	Vgs = -4.5V, Vds = -10V
Gate-Drain Charge	Qgd	_	1.6	_	nC	1D = -4A
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.2	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	3.4	_	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	23	_	ns	$R_L$ = 3.3Ω, $R_G$ = 1Ω
Turn-Off Fall Time	tF	_	9.6	_	ns	
Reverse Recovery Time	t <sub>RR</sub>	_	1.8	_	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	_	9.4	_	nC	IF = -1.0A, di/dt = 100A/µs

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.





 $I_D = -1mA$ 

75

125

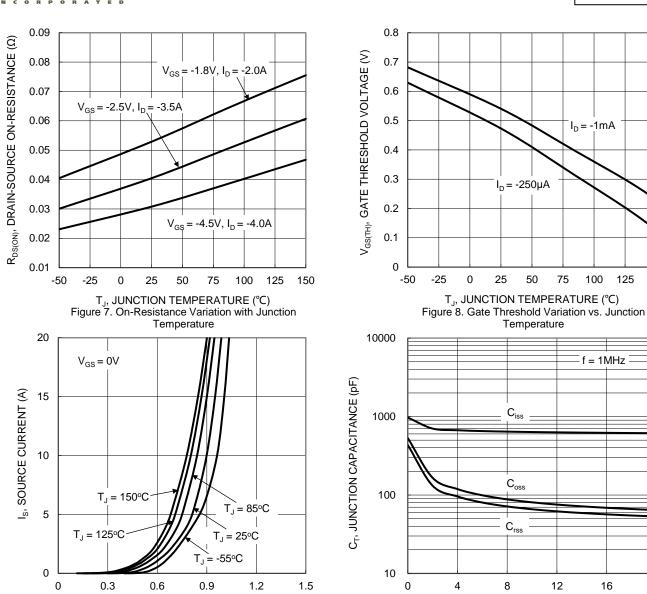
150

20

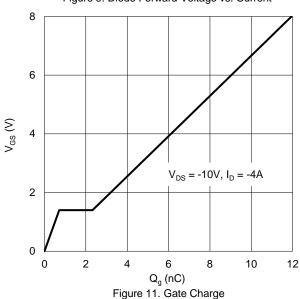
100

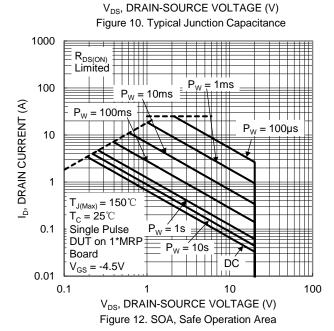
f = 1MHz





V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current







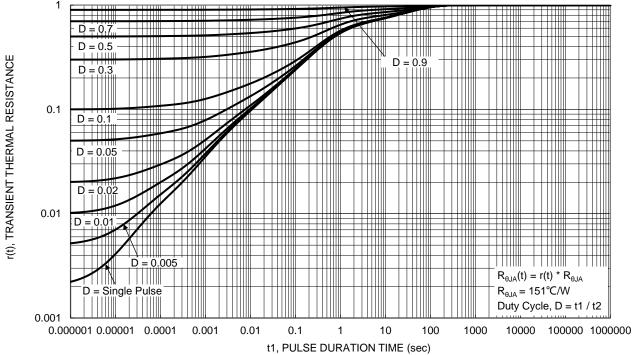


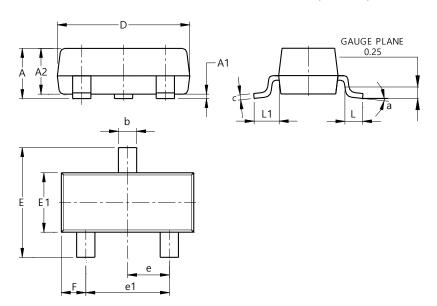
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)

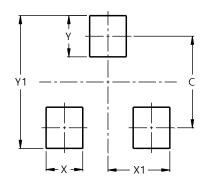


SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	<b>L</b> 0.25		0.40				
а	0°	8°					
All	Dimens	ions in	mm				

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	29



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